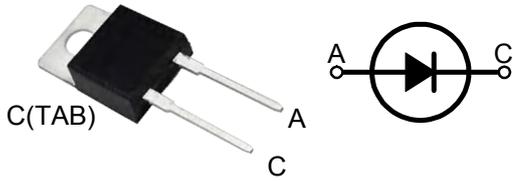


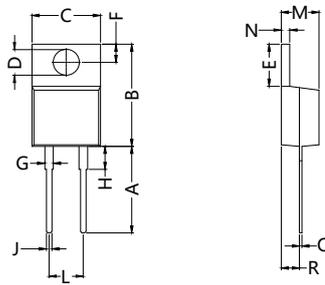
# MBR850 thru MBR860

## High Tjm Low IRRM Schottky Barrier Diodes



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-220AC



Dim.	Millimeter	
	Min.	Max.
A	12.70	13.97
B	14.73	16.00
C	9.91	10.66
ØD	3.54	4.08
E	5.85	6.85
F	2.54	3.18
G	1.15	1.65
H	2.79	5.84
J	0.64	1.01
L	5.05BSC	
M	4.32	4.82
N	1.14	1.39
Q	0.35	0.56
R	2.29	2.79



	V <sub>RRM</sub> V	V <sub>RMS</sub> V	V <sub>DC</sub> V
<b>MBR850</b>	50	35	50
<b>MBR860</b>	60	42	60

Symbol	Characteristics	Maximum Ratings	Unit
I <sub>(AV)</sub>	Maximum Average Forward Rectified Current @T <sub>c</sub> =125 °C	8	A
I <sub>FSM</sub>	Peak Forward Surge Current 8.3ms Single Half-Sine-Wave Superimposed On Rated Load (JEDEC METHOD)	150	A
dv/dt	Voltage Rate Of Change (Rated V <sub>R</sub> )	10000	V/us
V <sub>F</sub>	Maximum Forward Voltage (Note 1) I <sub>F</sub> =8A @T <sub>J</sub> =125°C I <sub>F</sub> =8A @T <sub>J</sub> =25°C I <sub>F</sub> =16A @T <sub>J</sub> =25°C	0.70 0.80 0.95	V
I <sub>R</sub>	Maximum DC Reverse Current At Rated DC Blocking Voltage @T <sub>J</sub> =25°C @T <sub>J</sub> =125°C	0.1 15	mA
R <sub>θJC</sub>	Typical Thermal Resistance (Note 2)	3.0	C/W
C <sub>J</sub>	Typical Junction Capacitance (Note 3)	250	pF
T <sub>J</sub>	Operating Temperature Range	-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +175	°C

NOTES: 1. 300us Pulse Width, Duty Cycle 2%.  
2. Thermal Resistance Junction To Case.  
3. Measured At 1.0MHz And Applied Reverse Voltage Of 4.0V DC.

### FEATURES

- \* Metal of silicon rectifier, majority carrier conduction
- \* Guard ring for transient protection
- \* Low power loss, high efficiency
- \* High current capability, low V<sub>F</sub>
- \* High surge capacity
- \* For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- \* Ü[ PUA { ] ] & ^

### MECHANICAL DATA

- \* Case: TO-220AC molded plastic
- \* Polarity: As marked on the body
- \* Weight: 2 grams
- \* Mounting position: Any

# MBR850 thru MBR860

## High $T_{jm}$ Low IRRM Schottky Barrier Diodes

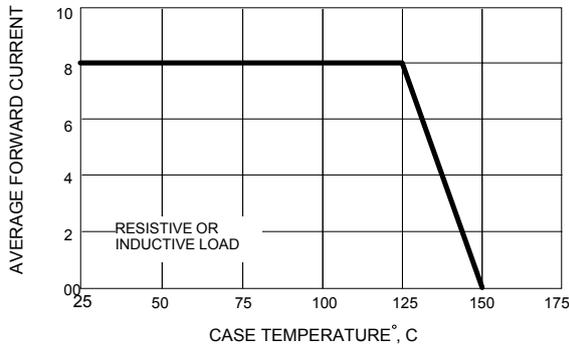


FIG. 1 - FORWARD CURRENT DERATING CURVE

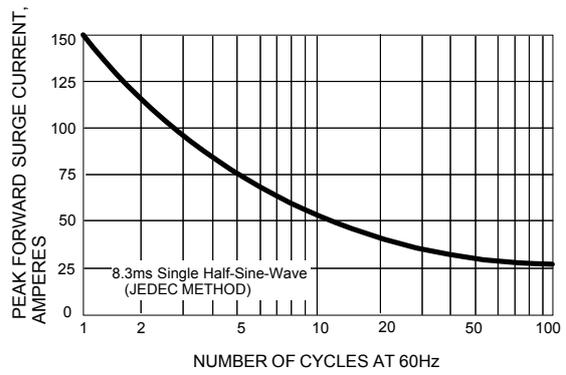


FIG. 2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

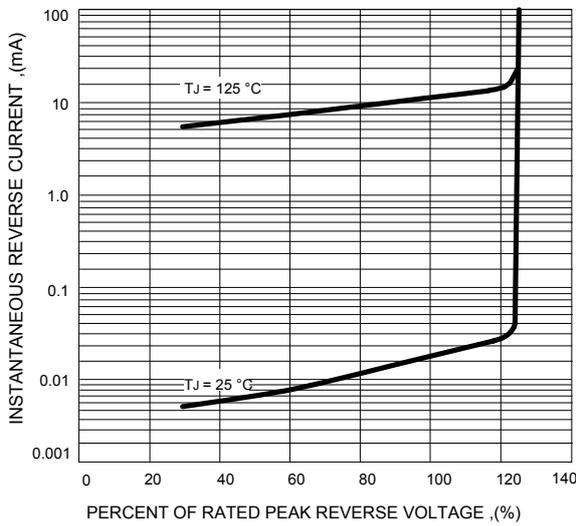


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

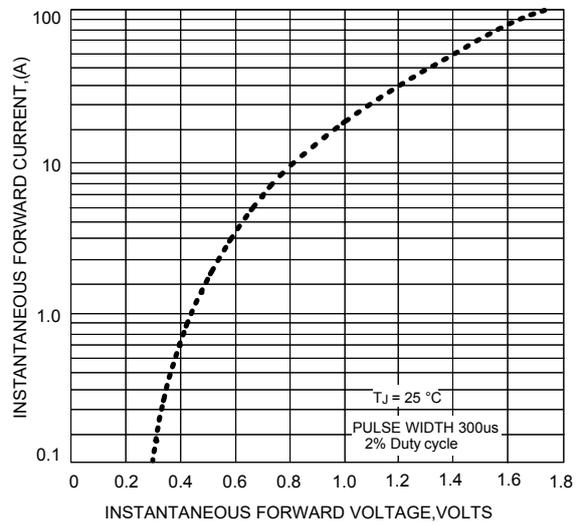


FIG. 4 - TYPICAL FORWARD CHARACTERISTICS

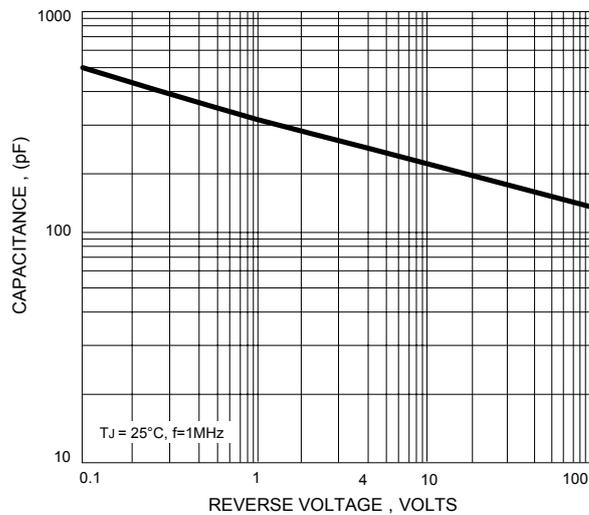
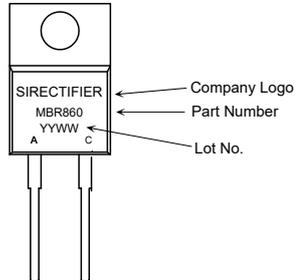


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

# MBR850 thru MBR860

## High Tjm Low IRRM Schottky Barrier Diodes

### Marking



### Ordering Information

Part Number	Package	Shipping	Marking Code
MBR850	TO-220AC	50pcs / Tube	MBR850
MBR860	TO-220AC	50pcs / Tube	MBR860